



An overview of Axion Dark Matter eXperiment: *current status and future plans*

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On the behalf of ADMX Collaboration

QCD Axion as dark matter

- Solution of the strong CP problem
- Cosmological production as cold dark matter: pre (wide mass range) or post ($1 \mu\text{eV} \sim 1 \text{meV}$)-inflation misalignment
- Wave-like: mass $\ll 10 \text{eV}$ with occupancy number

$$N \approx \frac{\rho_{\text{DM}}}{m} \lambda_{\text{dB}}^3 \gg 1$$

De Broglie wavelength

$$\lambda_{\text{dB}} \approx \frac{2\pi}{mv}$$

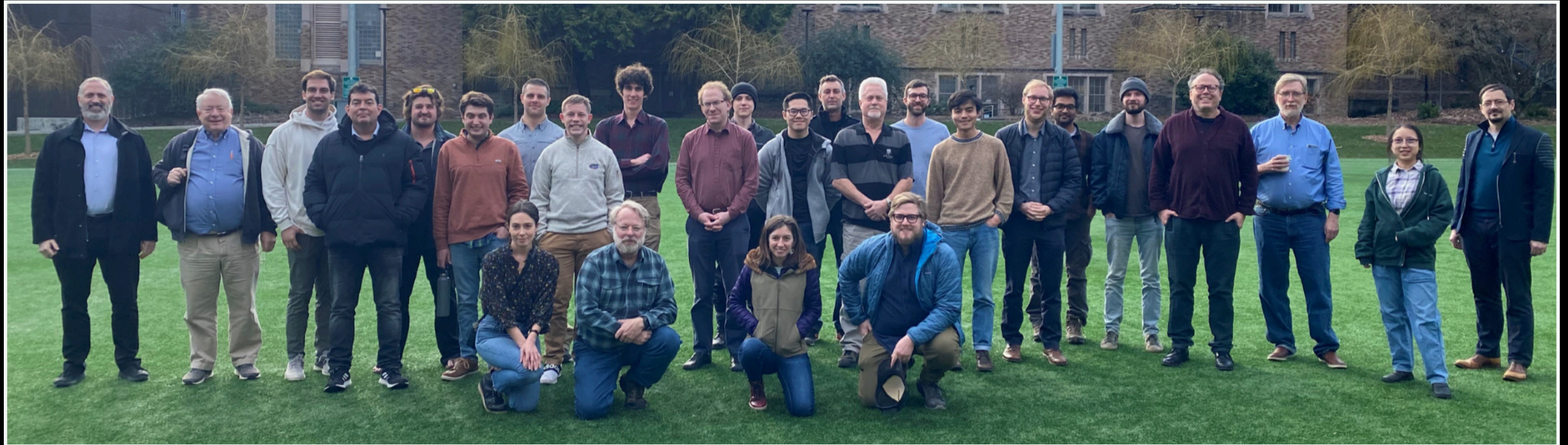
WIMP dark matter ($m \sim 100 \text{GeV}$)

$\lambda_{\text{dB}} \sim 10^{-13} \text{m}$

Axion dark matter ($m \sim 10^{-6} \text{eV}$)

$\lambda_{\text{dB}} \sim 100 \text{m}$

ADMX Collaboration



HEISING - SIMONS
FOUNDATION



Pacific
Northwest
NATIONAL
LABORATORY



GEORG-AUGUST-UNIVERSITÄT
GÖTTINGEN



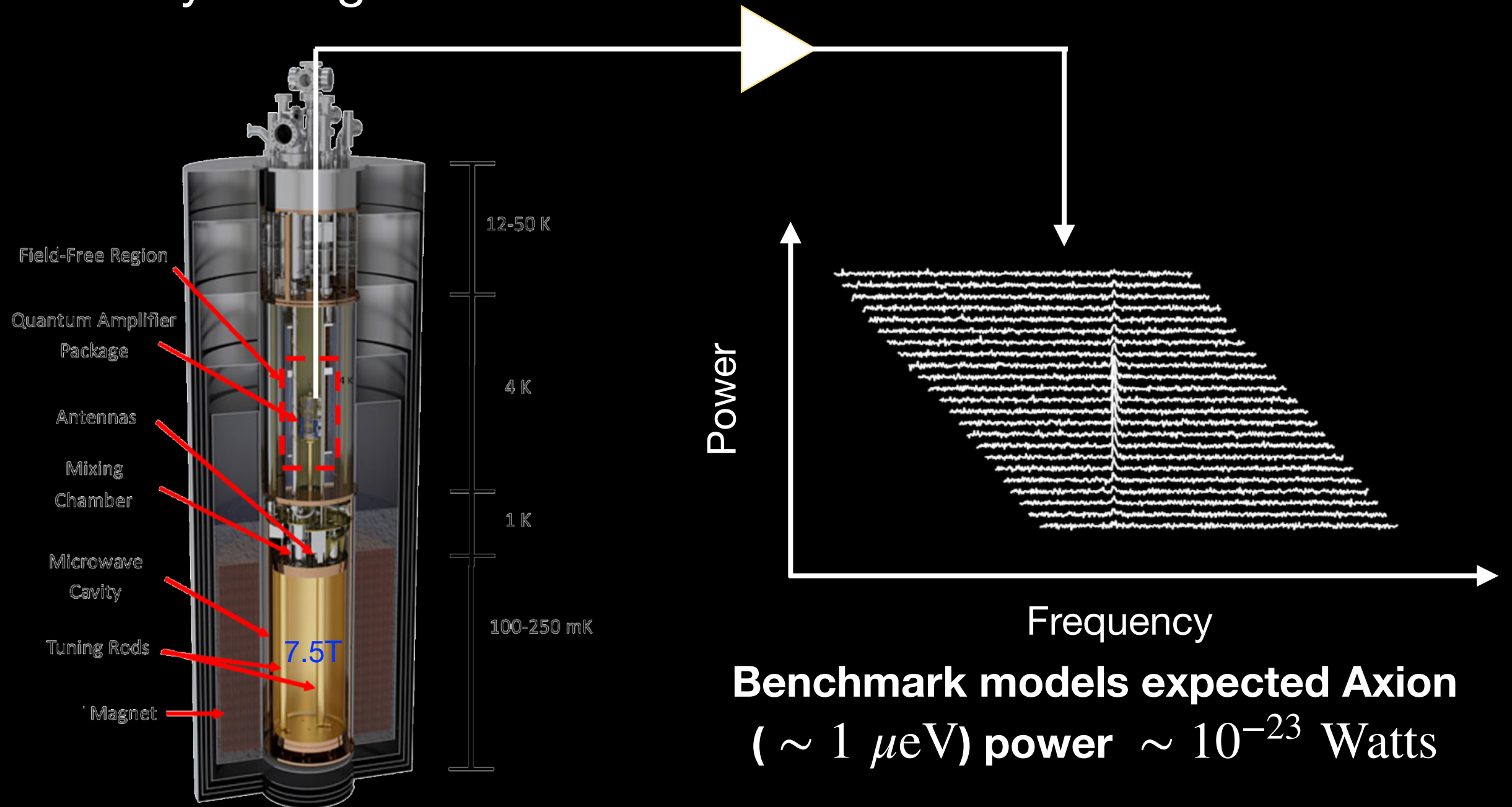
Berkeley
UNIVERSITY OF CALIFORNIA

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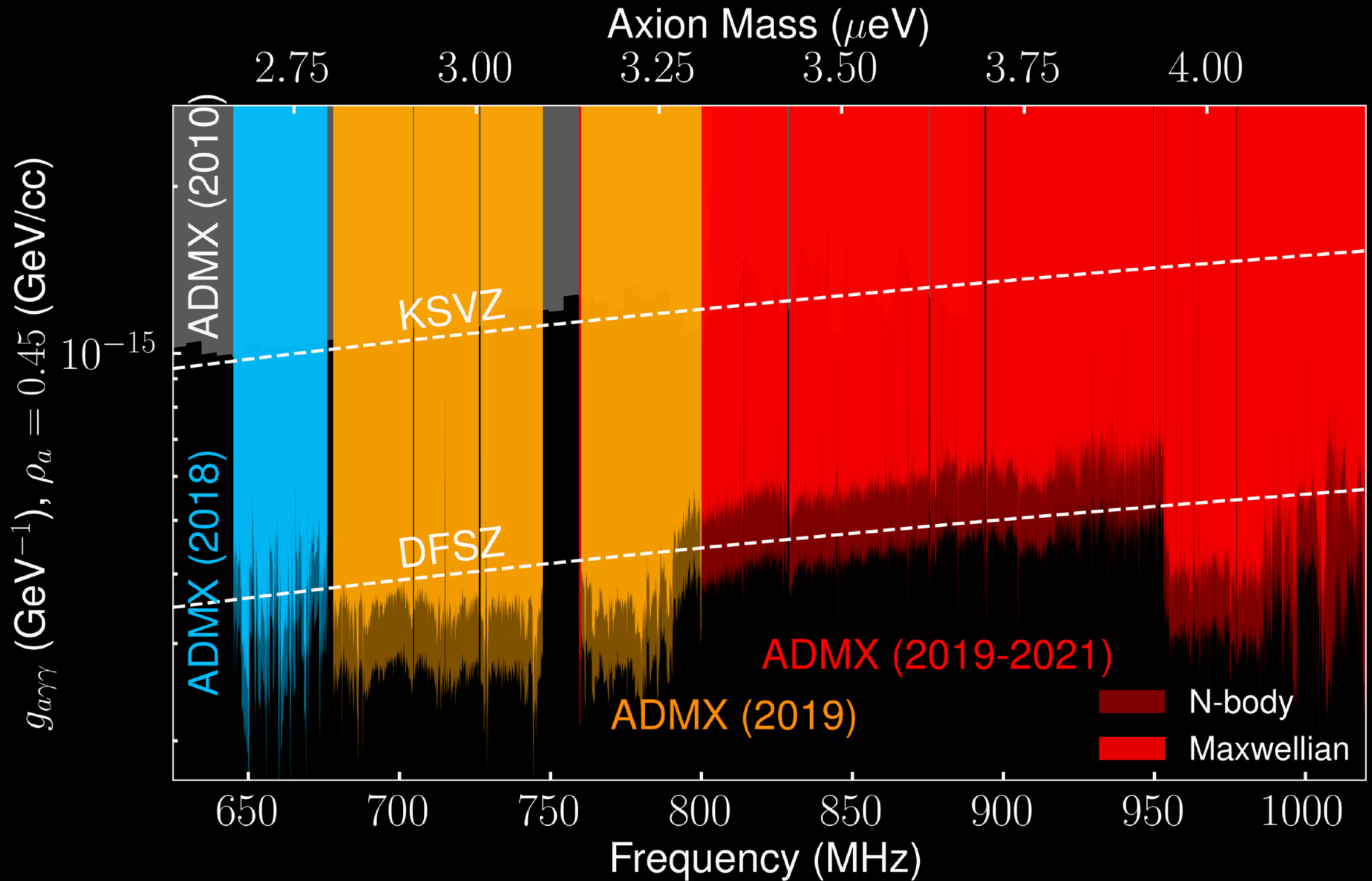
ADMX design (axion haloscope)

P. Sikivie, Phys. Rev. Lett. 51, 1415 (1983)

- Search on axion decay into photons: $g_{a\gamma\gamma}$
- Primary background: thermal noise

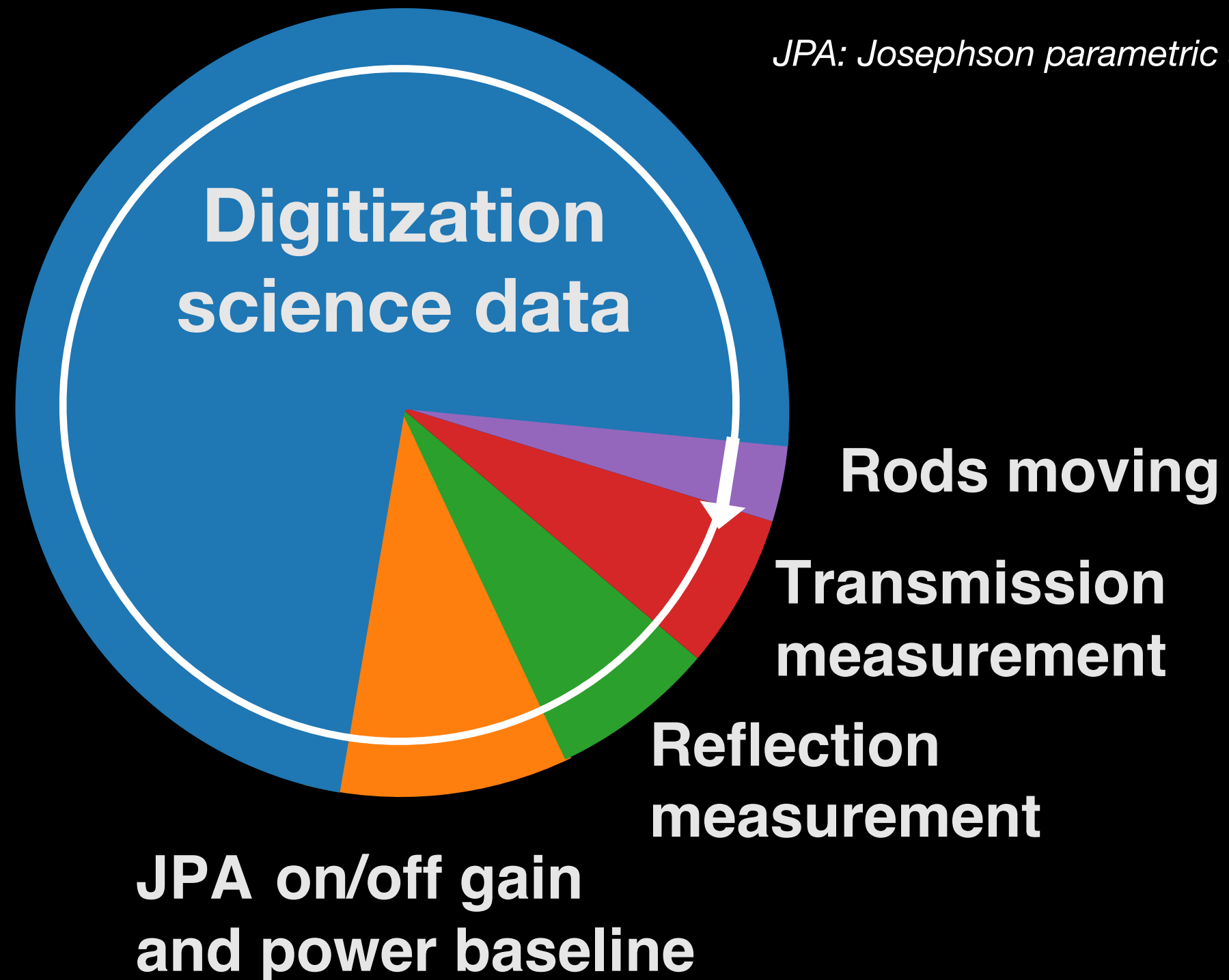


ADMX Gen 2-Run1: published data

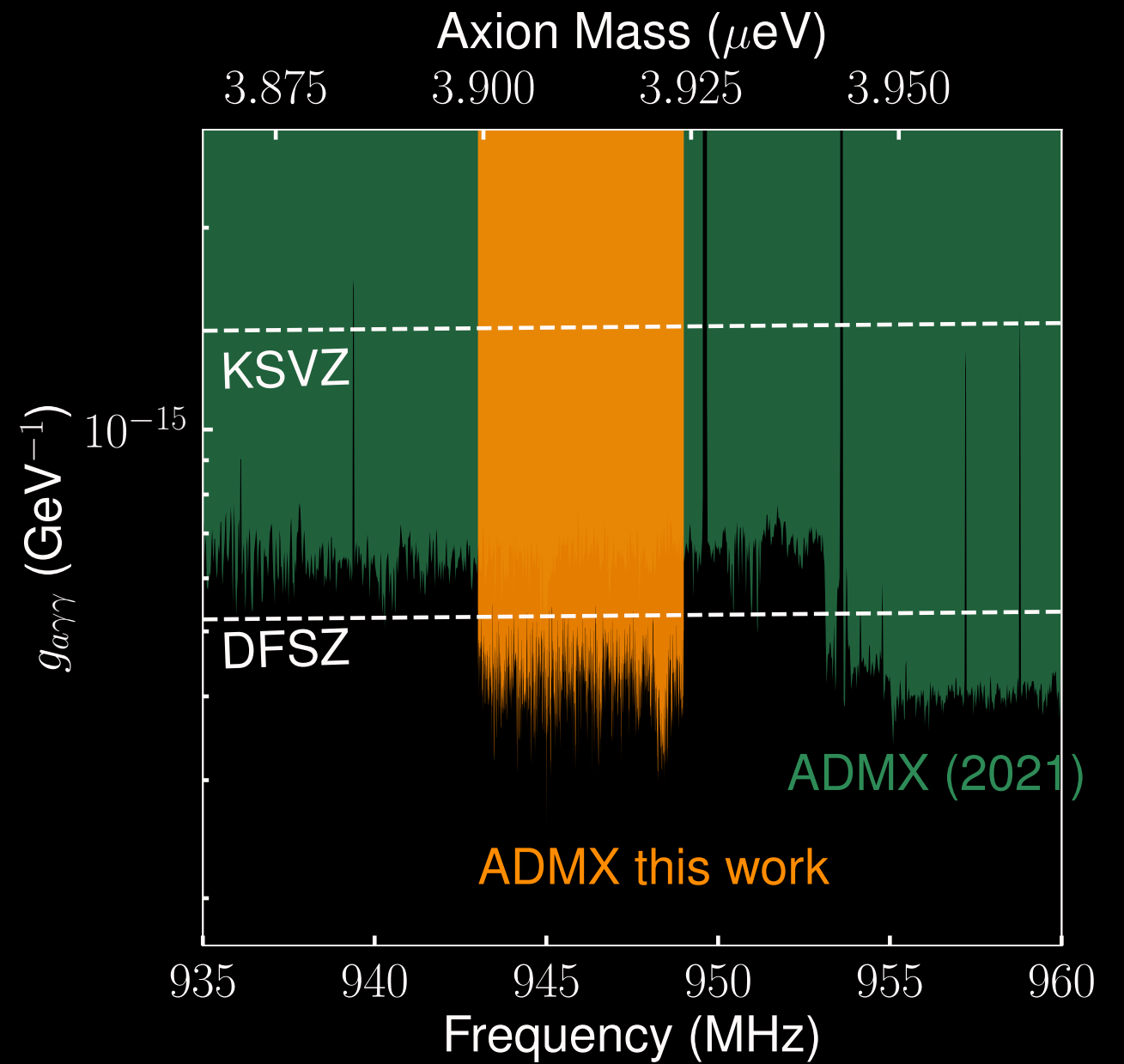
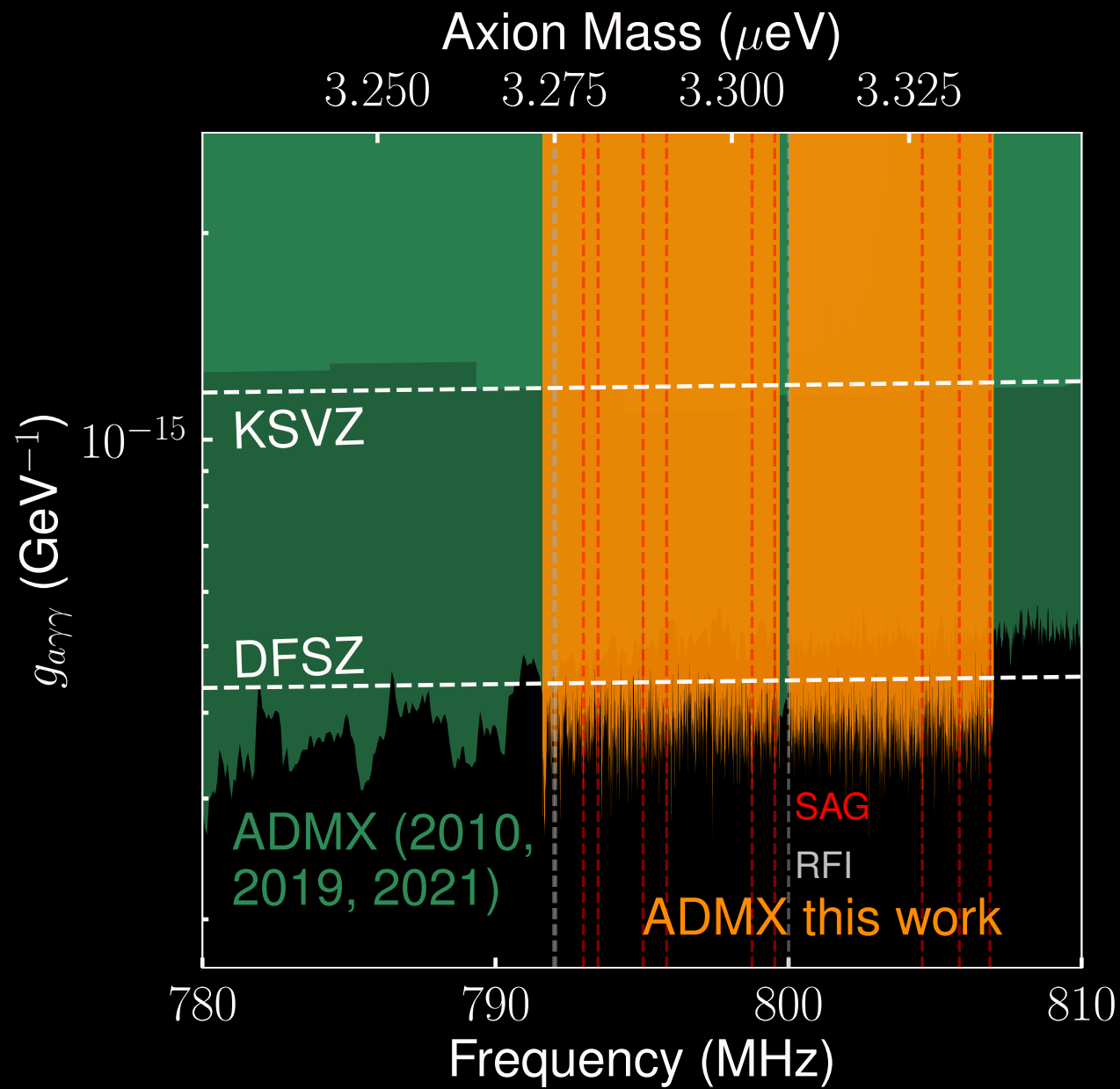


Fraction of operation time by task

- 20 MHz in 5 months for DFSZ sensitivity



Preliminary sensitivity



SAG: synthetic axion generator
RFI: radio frequency interference

ADMX: Gen2 future plan 1

- Hardware upgrades on-going
- 1020 to 1350 MHz (plan to start this summer)



Cavity with
one bigger tuning rod

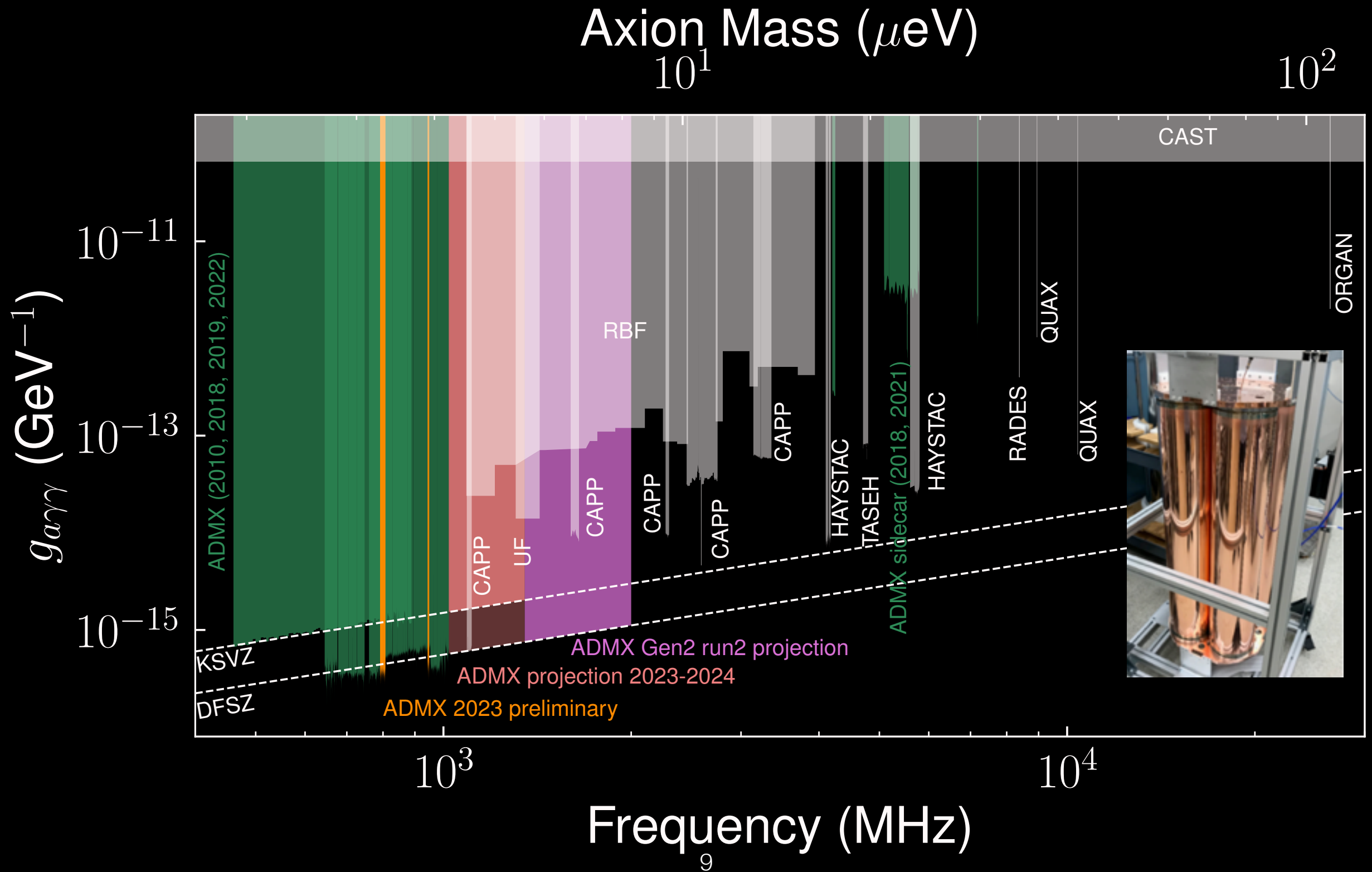


Cold electronics
including JPA



ADMX Gen2 future plan 2

- Four-cavity array, up to 2 GHz



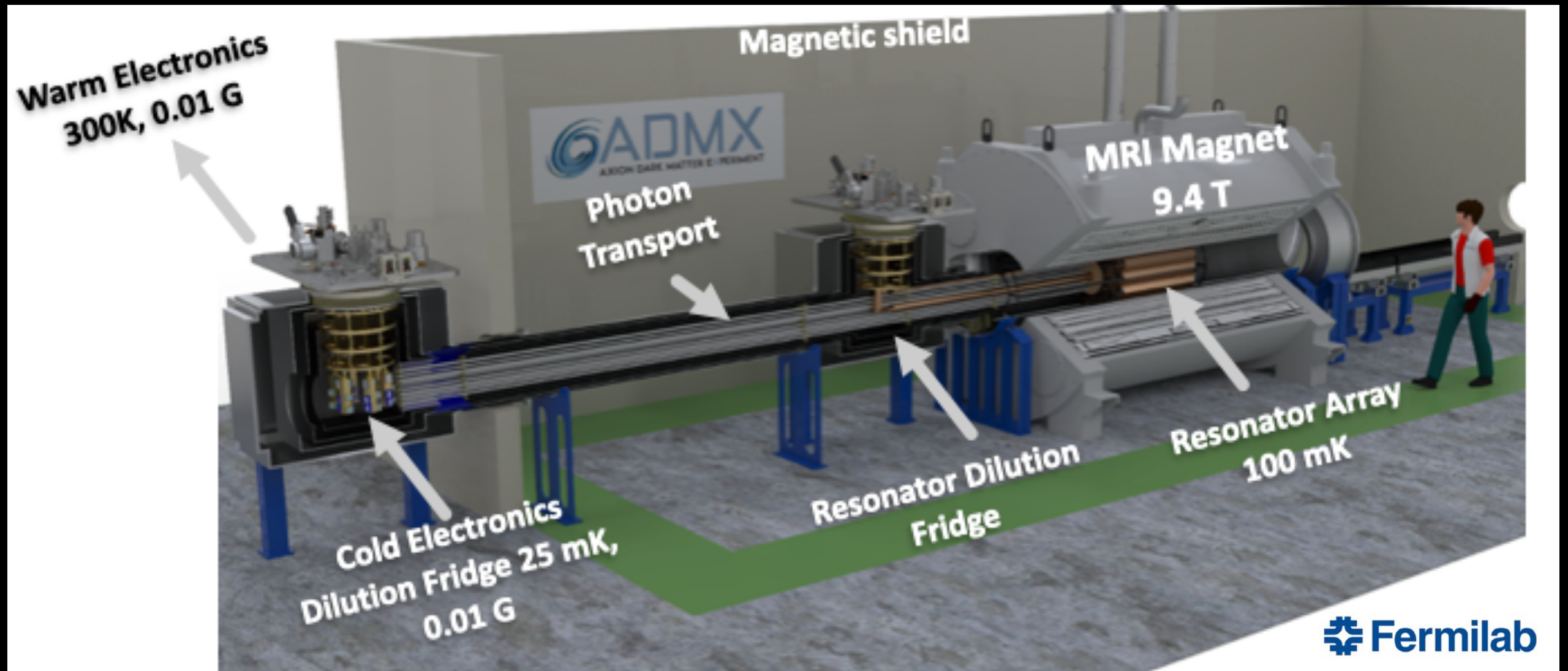
ADMX Extended Frequency Range (2–4 GHz)

MRI magnet

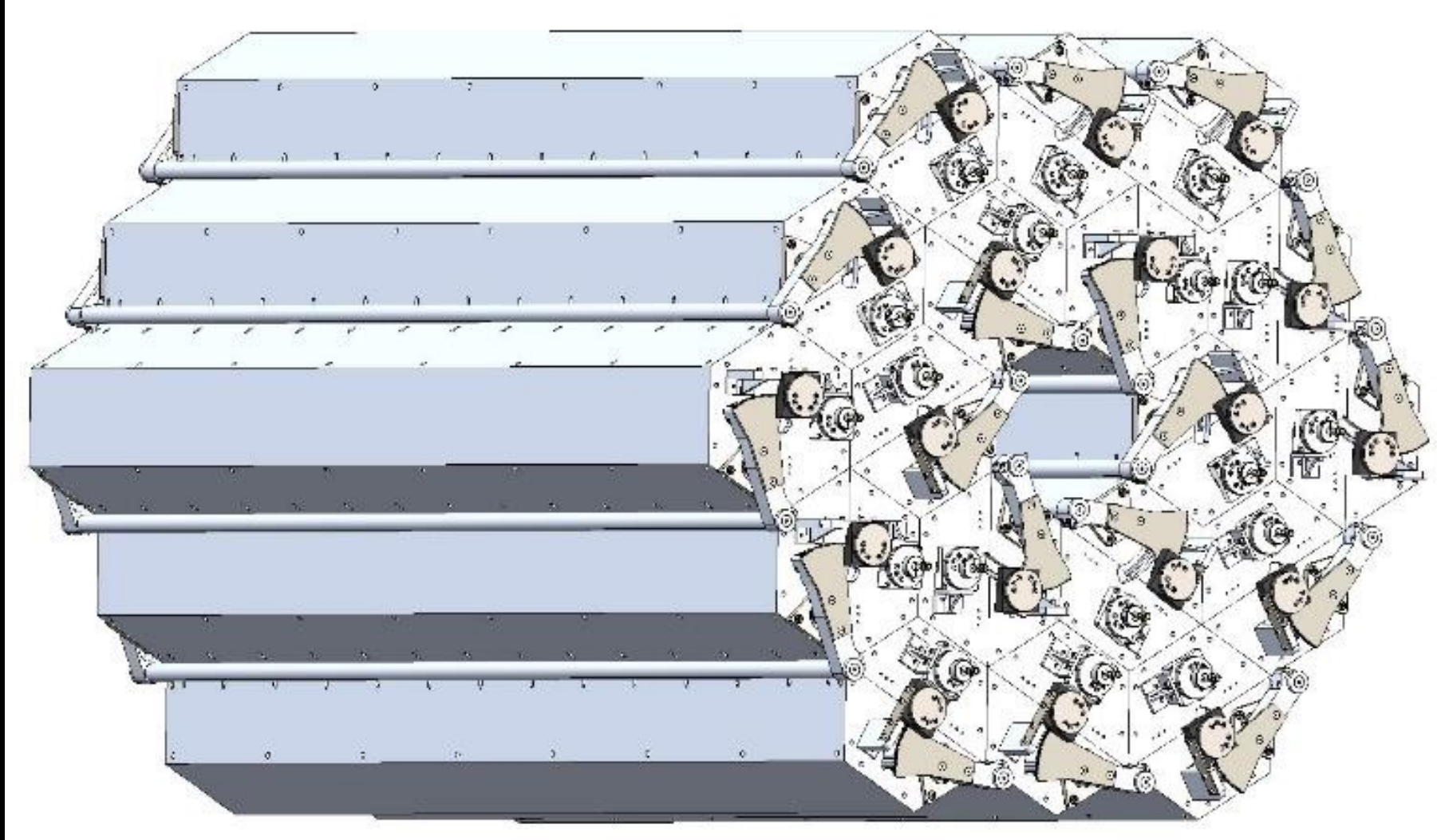
University of Illinois Chicago (UIC)
Manufactured by GE Healthcare in 2003

$B \approx 9.4\text{T}$

$\sim 80\text{ cm warm bore}$



ADMX-EFR: More Cavities



- 18-cavity array
- 2-4 GHz

$V \sim 250$ L (almost doubled to now)

Scan speed [Hz/s]:
 $\propto B^4 V^2 \sim \times 5$ of current ADMX

Conclusion

- Sensitivity has reached to the most promising QCD Axion benchmark model with quantum devices!
- ADMX future:
 - Search higher axion masses (near)
 - Even higher masses with multiple-cavity detectors (Gen2 and EFR)

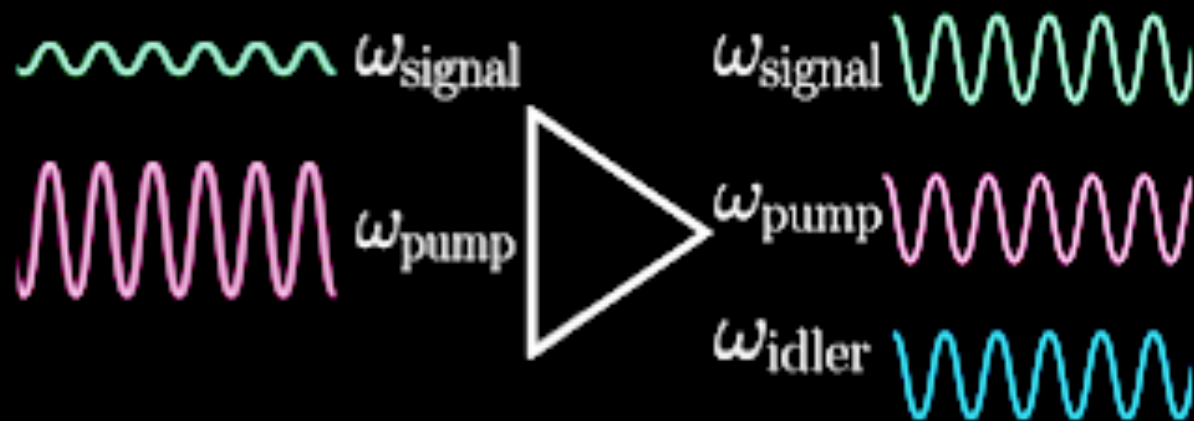
Discovery could come at any time!

Backup

$$P_{\text{axion}} = 7.7 \times 10^{-23} \text{ W} \left(\frac{V}{136 \ell} \right) \left(\frac{B}{7.5 \text{ T}} \right)^2 \left(\frac{C}{0.4} \right) \times$$
$$\left(\frac{g_\gamma}{0.36} \right)^2 \left(\frac{\rho_a}{0.45 \text{ GeV/cc}} \right) \left(\frac{f}{1 \text{ GHz}} \right) \left(\frac{Q_L}{80,000} \right).$$

ADMX Gen2 with quantum amplifiers

- Josephson Parametric Amplifiers (JPAs)
 - Ideal for higher frequency range searches (current main)
 - Narrowband gain



Figures courtesy of Shahid Jawas

$$N_{\text{tot}} = N(T_{\text{sig}}, \omega_{\text{signal}}) + N(T_{\text{idler}}, \omega_{\text{idler}})$$



*JPA provided by
Siddiq Group at UC Berkeley*

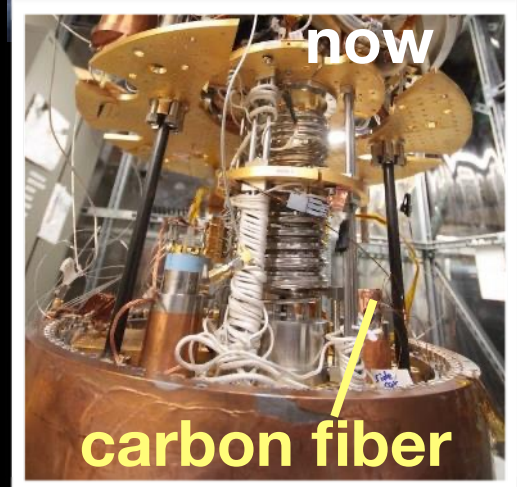
Noise temperature

- Low noise receiver
 - JPA (T_{signal} 140mK, T_{idler} 100mK) + Heterostructure Field Effect Transistor (HFET) amp (4K) + Post-amp (RT)

Heat flow: 70 \rightarrow 12 μ W

T_{phy} : 150 \rightarrow 100 mK

1GHz~50mK
(standard quantum limit)



More than 100 mK improvement in T_{sys} reached

$$\text{SNR} = \frac{P_{\text{axion}}}{\sigma} = \frac{P_{\text{axion}}}{k_B T_{\text{sys}}} \sqrt{\frac{t}{b}}$$

$$T_{\text{sys}} = \frac{T_{\text{HFET}}/\epsilon}{\text{SNRI}} \rightarrow$$

in-situ

$$\text{SNRI} = \frac{G_{\text{on}} P_{\text{off}}}{G_{\text{off}} P_{\text{on}}}$$

